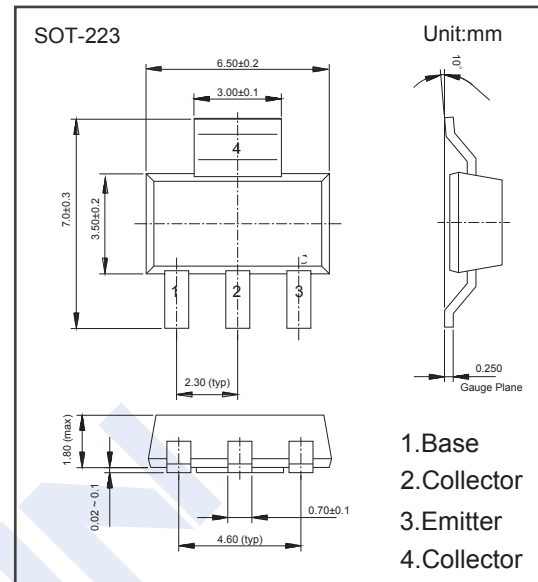
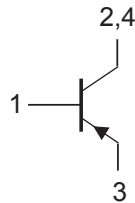


PNP Transistors 2KB4017

■ Features

- High current (max. 1 A)
- Medium power (max. 1.3 W).
- Complements to 2KD3009



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-100	V
Collector - Emitter Voltage	V _{CE0}	-80	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _C	-1	A
Collector Current - Pulse	I _{CP}	-1.5	
Base Current - Pulse	I _{BP}	-0.2	
Collector Power Dissipation	P _C	1.3	W
Thermal Resistance from Junction to Ambient	R _{θJA}	95	°C/W
Thermal Resistance from Junction to Soldering Point	R _{θJS}	14	
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

PNP Transistors

2KB4017

Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}$, $I_E = 0$	-100			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}$, $I_B = 0$	-80			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}$, $I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -80 \text{ V}$, $I_E = 0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -2 \text{ V}$, $I_C = -500 \text{ mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -2 \text{ V}$, $I_C = -5 \text{ mA}$	40			
		$V_{CE} = -2 \text{ V}$, $I_C = -150 \text{ mA}$	63		250	
		$V_{CE} = -2 \text{ V}$, $I_C = -500 \text{ mA}$	25			
Transition frequency	f_T	$V_{CE} = -5 \text{ V}$, $I_C = -10 \text{ mA}$, $f = 100 \text{ MHz}$		115		MHz

Marking

Marking	2KE K****
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Typical Characteristics

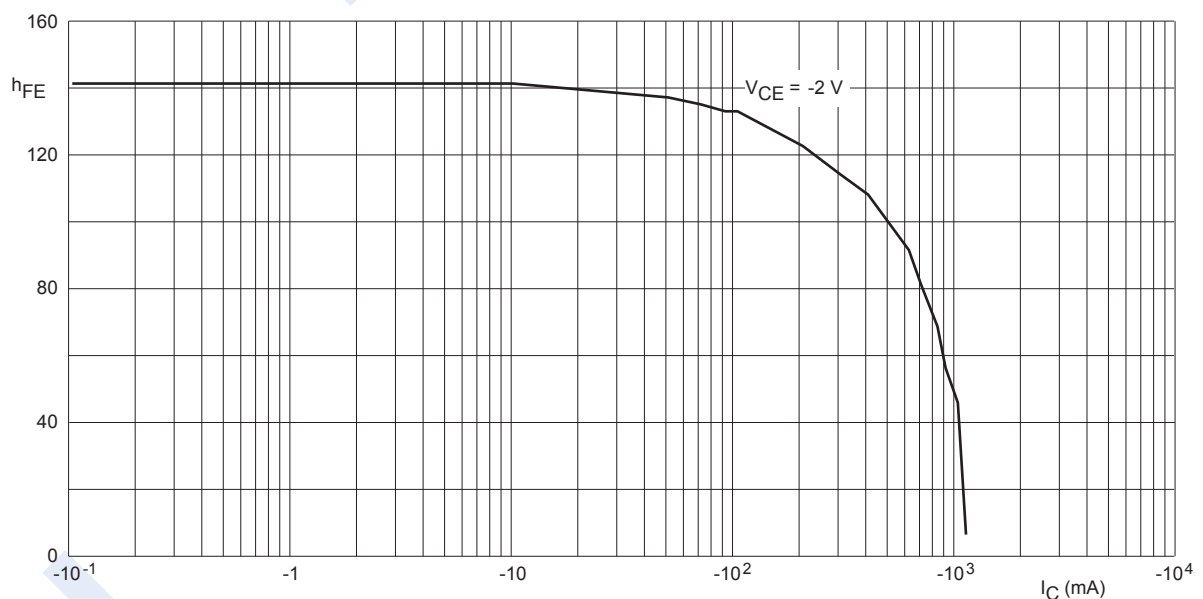


Fig.1 DC current gain; typical values.